

SiC Schottky Barrier Diode

TRS30N120HB

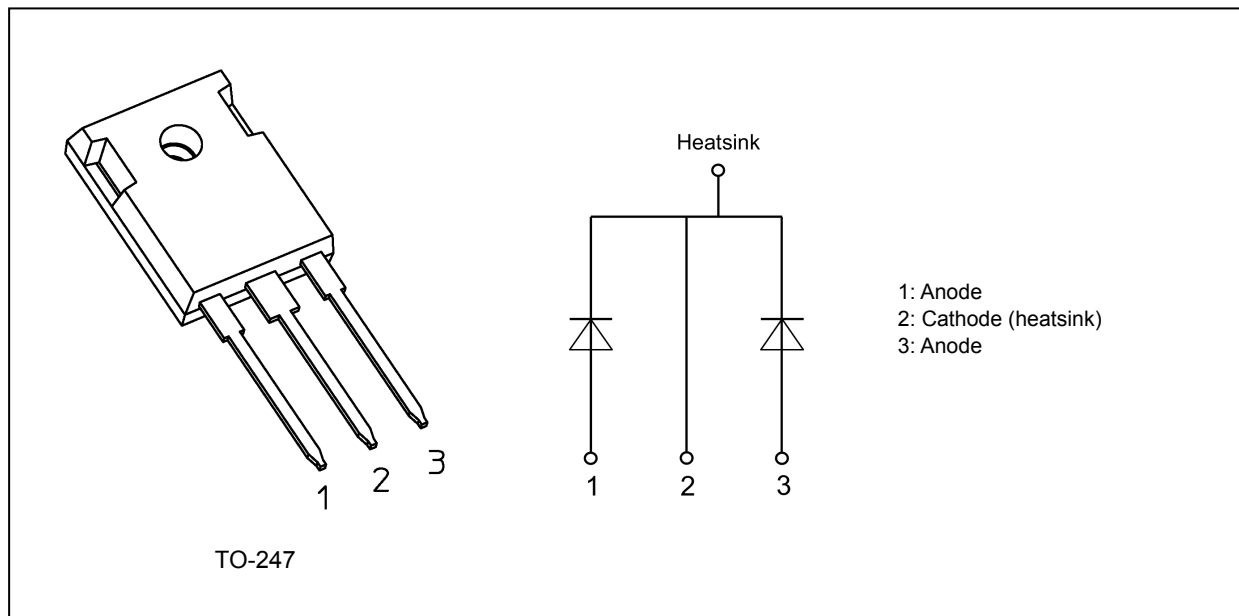
1. Applications

- Power Factor Correction
- Solar Inverters
- Uninterruptible Power Supplies
- DC-DC Converters

2. Features

- (1) Chip design of 3rd generation
- (2) Low forward voltage : V_F (Per Leg) = 1.27 V (typ.)
- (3) Low total capacitive charge: Q_c (Per Leg) = 80 nC (typ.)
- (4) Low reverse current: I_R (Per Leg) = 1.4 μ A (typ.)

3. Packaging and Internal Circuit



Start of commercial production
2024-07

4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$)

Characteristics	Symbol	Note	Test Condition	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}			1200	V
Forward DC current	$I_{F(DC)}$	(Note1)	Per Leg	15	A
			Both Legs	30	
		(Note2)	Per Leg	41	
			Both Legs	82	
Non-repetitive peak forward surge current	I_{FSM}	(Note3)	Per Leg	105	A
			Both Legs	210	
		(Note4)	Per Leg	90	
			Both Legs	180	
		(Note5)	Per Leg	940	
			Both Legs	1880	
Power dissipation	P_D	(Note2)	Per Leg	197	W
			Both Legs	394	
Junction temperature	T_j			175	$^{\circ}\text{C}$
Storage temperature	T_{stg}			-55 to 175	$^{\circ}\text{C}$
Mounting torque	TOR			0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note1: $T_c = 150\text{ }^{\circ}\text{C}$

Note2: $T_c = 25\text{ }^{\circ}\text{C}$

Note3: $f = 50\text{ Hz}$ (half-sine wave, $t = 10\text{ ms}$), $T_c = 25\text{ }^{\circ}\text{C}$

Note4: $f = 50\text{ Hz}$ (half-sine wave, $t = 10\text{ ms}$), $T_c = 150\text{ }^{\circ}\text{C}$

Note5: Square wave, $t = 10\text{ }\mu\text{s}$, $T_c = 25\text{ }^{\circ}\text{C}$

5. Thermal Characteristics

Characteristics	Symbol	Note	Test Condition	Max	Unit
Thermal resistance (junction-to-case)	$R_{th(j-c)}$	(Note1)	Per Leg	0.76	$^{\circ}\text{C/W}$
			Both Legs	0.38	
Thermal resistance (junction-to-ambient)	$R_{th(j-a)}$	(Note2)	—	50	

Note1: $T_c = 25\text{ }^{\circ}\text{C}$

Note2: $T_a = 25\text{ }^{\circ}\text{C}$

6. Electrical Characteristics (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$) (Per Leg)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Forward voltage (pulse measurement)	V_F	$I_F = 7.5\text{ A}$	—	1.0	—	V
		$I_F = 15\text{ A}$	—	1.27	1.45	
		$I_F = 15\text{ A}$, $T_a = 150\text{ }^{\circ}\text{C}$	—	1.64	—	
Reverse current (pulse measurement)	I_R	$V_R = 1200\text{ V}$	—	1.4	100	μA
		$V_R = 1200\text{ V}$, $T_a = 150\text{ }^{\circ}\text{C}$	—	14	—	
Total capacitance	C_t	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$	—	1628	—	pF
		$V_R = 800\text{ V}$, $f = 1\text{ MHz}$	—	54	—	
		$V_R = 1200\text{ V}$, $f = 1\text{ MHz}$	—	52	—	
Total capacitive charge	Q_c	$V_R = 800\text{ V}$, $f = 1\text{ MHz}$	—	80	—	nC

7. Marking (Note)

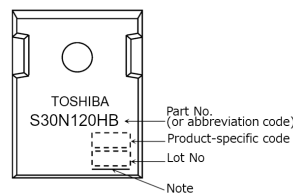


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.
[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.
The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Abbreviation Code	Part Number
S30N120HB	TRS30N120HB

8. Usage Considerations

For other design considerations, see the Toshiba website.

9. Characteristics Curves (Note)

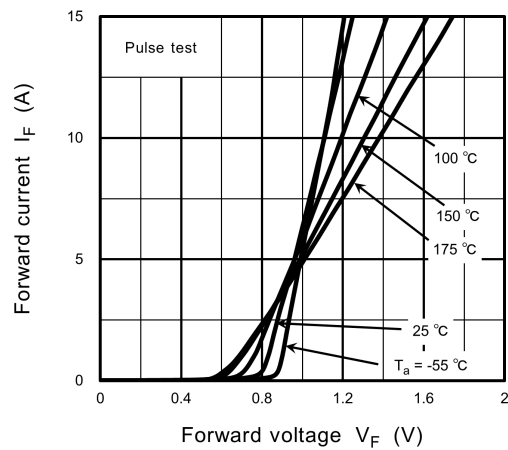


Fig. 9.1 $I_F - V_F$ (Per Leg)

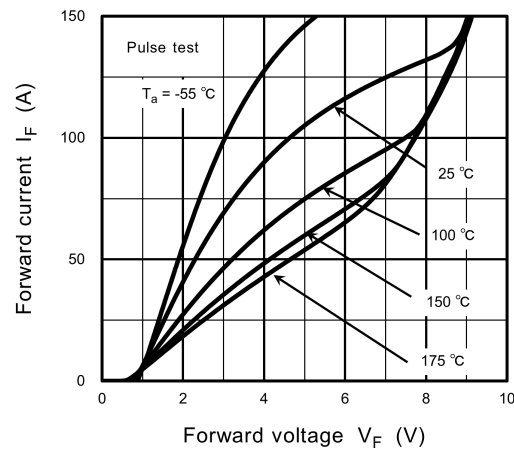


Fig. 9.2 $I_F - V_F$ (Per Leg)

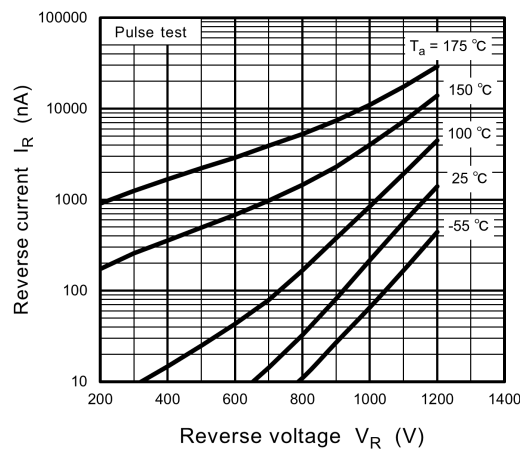


Fig. 9.3 $I_R - V_R$ (Per Leg)

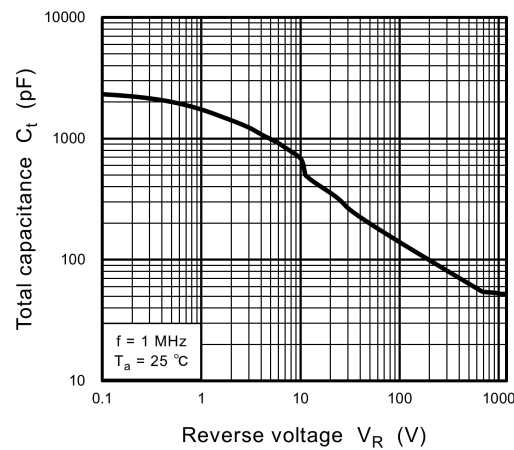


Fig. 9.4 $C_t - V_R$ (Per Leg)

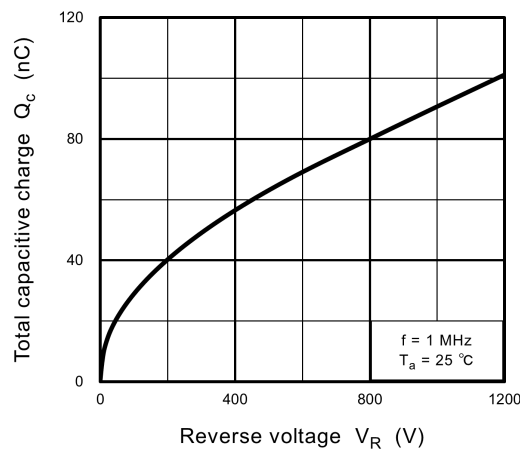


Fig. 9.5 $Q_C - V_R$ (Per Leg)

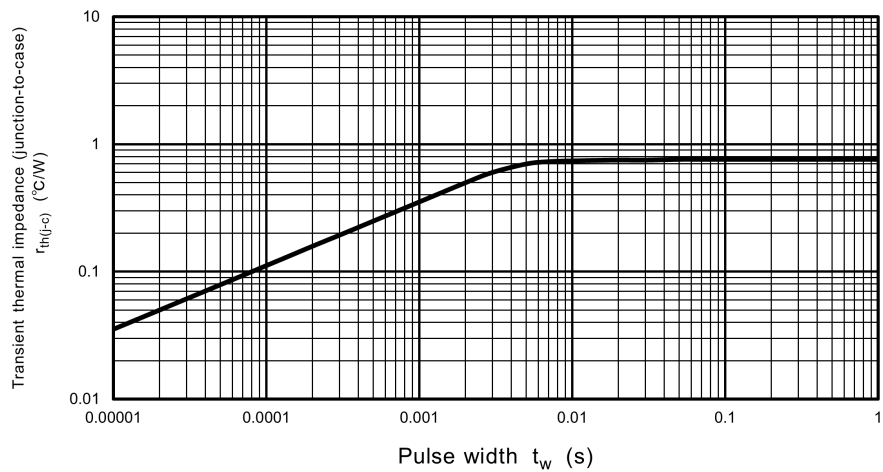


Fig. 9.6 $r_{th(j-c)}$ - t_w (Per Leg)
(Guaranteed Maximum)

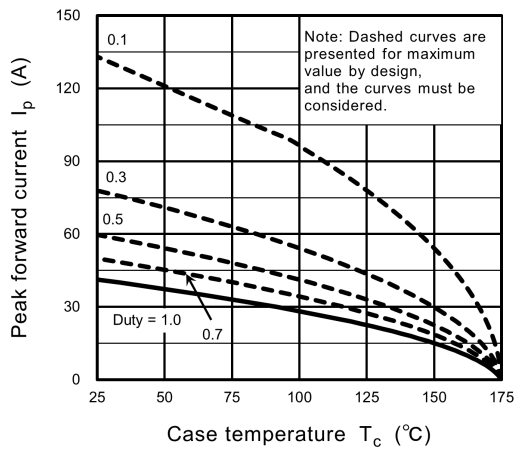


Fig. 9.7 I_p - T_c (Per Leg)

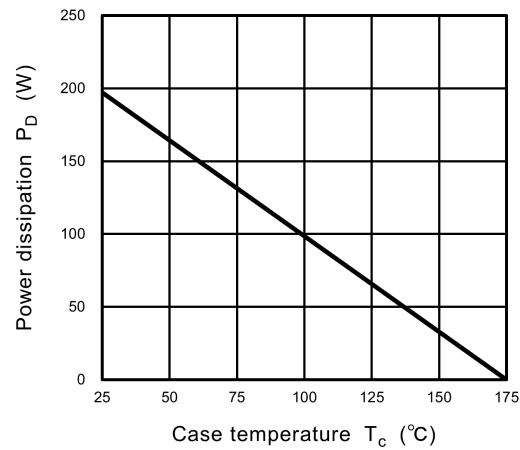
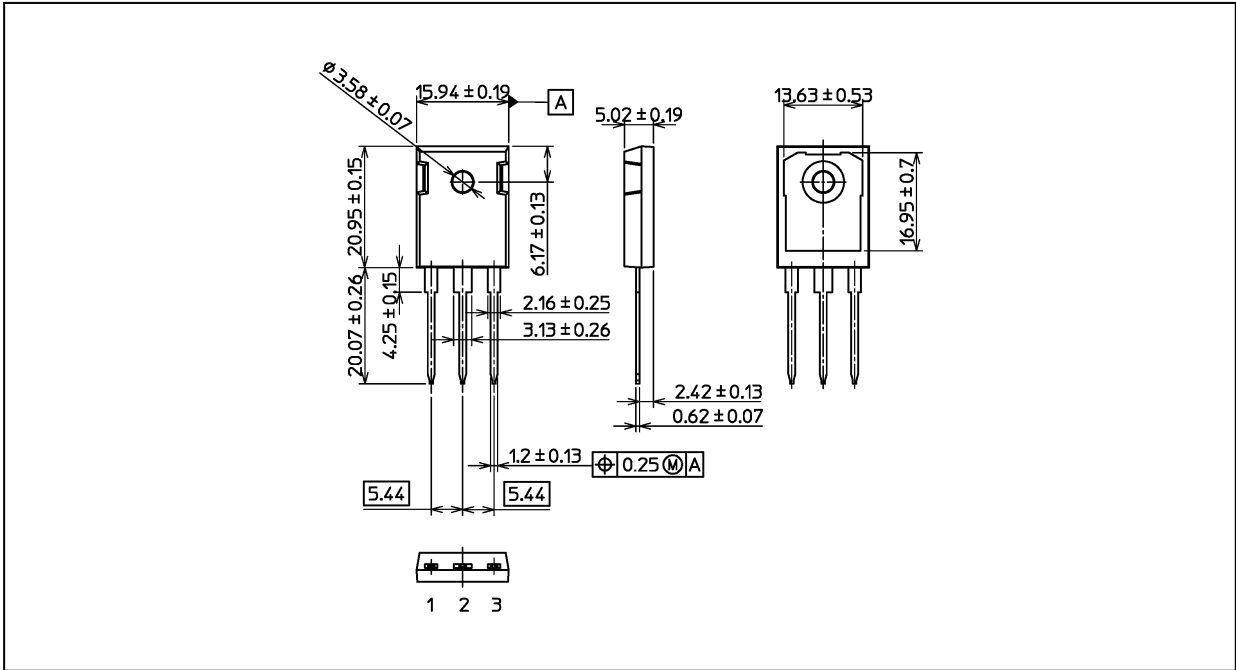


Fig. 9.8 P_D - T_c (Per Leg)
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

Package Name(s)
TOSHIBA: 2-16L1A
Nickname: TO-247

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